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J. Perkins, M. van Hest, C. Teplin, J. Alleman,
M. Dabney, L. Gedvilas, B. Keyes, B. To, and
D. Ginley
National Renewable Energy Laboratory

M. Taylor and D. Readey
Colorado School of Mines

A. Delahoy and S. Guo
Energy Photovoltaics, Inc.

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Application of Combinatorial Tools for Solar Cell Improvement – New High Performance Transparent Conducting Oxides

J. Perkins*, M. Taylor¹, M. van Hest, C. Teplin, J. Alleman, M. Dabney, L. Gedvilas, B. Keyes, B. To, A. Delahoy², S. Guo², D. Readey¹ and D. Ginley

National Renewable Energy Laboratory, Golden, CO 80401

¹Colorado School of Mines, Golden, CO 80401

²Energy Photovoltaics, Inc., Princeton, NJ 08543

*john_perkins@nrel.gov

ABSTRACT

Transparent conducting oxides (TCOs) can serve a variety of important functions in thin film photovoltaics such as transparent electrical contacts, antireflection coatings and chemical barriers. Two areas of particular interest are TCOs that can be deposited at low temperatures and TCOs with high carrier mobilities. We have employed combinatorial high-throughput approaches to investigate both these areas. Conductivities of $\approx 2500 \text{ } \Omega^{-1}\text{-cm}^{-1}$ have been obtained for In-Zn-O (IZO) films deposited at $100 \text{ } ^\circ\text{C}$ and $> 5000 \text{ } \Omega^{-1}\text{-cm}^{-1}$ for In-Ti-O (ITiO) and In-Mo-O (IMO) films deposited at $550 \text{ } ^\circ\text{C}$. The highest mobility obtained was $83 \text{ cm}^2/\text{V-sec}$ for ITiO deposited at $550 \text{ } ^\circ\text{C}$.

1. Introduction

Transparent conducting oxides (TCOs) can serve a variety of important functions in thin film photovoltaics such as transparent electrical contacts, antireflection coatings and chemical barriers [1]. Two areas of particular interest are TCOs that can be deposited at low temperatures and TCOs with high carrier mobilities. We have employed combinatorial high-throughput approaches to investigate both these areas [2,3].

2. Experimental Approach

Compositionally graded samples (“libraries”) are deposited by co-sputtering onto $2'' \times 2''$ glass substrates. Three to five libraries are generally required to cover the full composition range for a binary tie-line, such as from In_2O_3 to ZnO . In this study, we report on new high performance In_2O_3 based materials substituted separately with Zn, Mo, and Ti [3-6]. After deposition and, in some cases, additional controlled atmosphere annealing, the libraries are characterized by a variety of automated combinatorial mapping tools. At present these include EPMA for metals stoichiometry, 4-pt. probe for sheet resistance, UV/VIS/NIR (200-2000nm) reflection and transmission, FTIR optical reflection and transmission (1.8 – 25 μm) and x-ray diffraction (XRD) using a large area 2D detector. For selected libraries, smaller samples are cut out for Hall effect measurements to determine the carrier concentration and mobility.

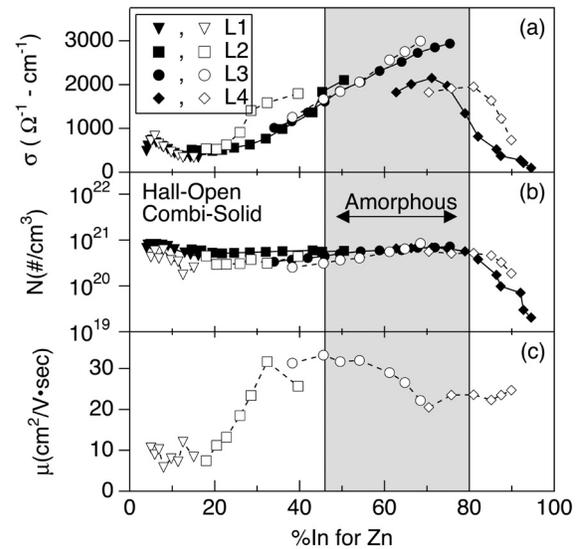


Fig. 1. Electrical conductivity (a), carrier concentration (b) and mobility (c) for In-Zn-O (IZO) deposited at $100 \text{ } ^\circ\text{C}$.

3. Results and Accomplishments

3.1 In-Zn-O (IZO)

For In-Zn-O (IZO) libraries deposited from ceramic oxide targets at $100 \text{ } ^\circ\text{C}$ in Ar with no post-deposition annealing, a broad maximum in the conductivity with $\approx 2500 \text{ } \Omega^{-1}\text{-cm}^{-1}$ is found for $x \sim 0.55$ to 0.75 in $\text{Zn}_{1-x}\text{In}_x\text{O}_y$ (Fig. 1a). This roughly correlates with the composition range found to be amorphous by the XRD mapping. For higher In content, the carrier concentration decreases (Fig 1b) and for lower In content, the mobility decreases (Fig 1c). For samples with a composition in the amorphous region, the conductivity is unchanged by annealing for one hour in air at $200 \text{ } ^\circ\text{C}$. Figure 2 shows the optical reflectivity from 0.3 to 25 μm for an IZO library compositionally centered on the conductivity maximum. These samples are transparent in the visible region as evident from the spectra shown in the top panel and, in both panels, the solid black circles show the approximate plasma wavelength (λ_p).

3.2 In-Mo-O (IMO)

For In-Mo-O (IMO) libraries deposited at $350 \text{ } ^\circ\text{C}$, a maximum in the conductivity with $\approx 1000 \text{ } \Omega^{-1}\text{-cm}^{-1}$ is found for $\sim 6\%$ Mo in place of In (Fig. 3a). Increasing the deposition temperature to $550 \text{ } ^\circ\text{C}$ results in a five fold increase in the maximum conductivity to $\approx 5000 \text{ } \Omega^{-1}\text{-cm}^{-1}$.

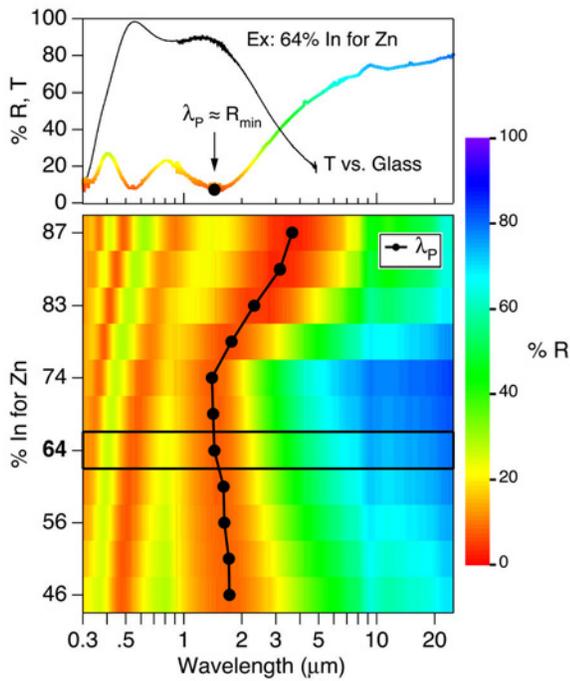


Fig. 2. Optical reflectance spectra for In-Zn-O (IZO) deposited at 100 °C.

This is due to increases in both the carrier concentration and the mobility (Fig. 3b). In particular, for IMO samples grown at 550 °C, the maximum mobility obtained is 65 $\text{cm}^2/\text{V}\cdot\text{sec}$ at ~ 4% Mo and the maximum carrier concentration is $6.6 \times 10^{20}/\text{cm}^3$ at ~ 8.5% Mo.

3.3 In-Ti-O (ITiO)

For ITiO libraries deposited at $T_s = 550 \text{ }^\circ\text{C}$, $\sigma \approx 5000 \text{ } \Omega^{-1}\cdot\text{cm}^{-1}$ for ~ 3 to 4 % Ti in place of In with a maximum mobility of $83 \text{ cm}^2/\text{V}\cdot\text{sec}$ at ~ 2 % Ti. For the sputtered ITiO samples, there is a linear increase in the carrier concentration of $3.4 \times 10^{20}/\text{cm}^3$ per %Ti from ~ 1.5 to 3 %

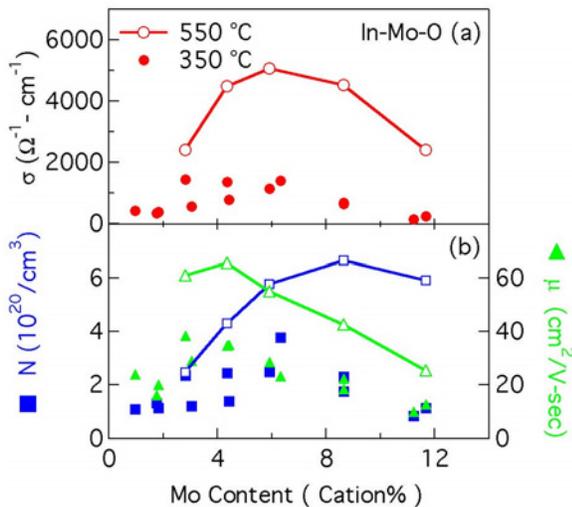


Fig. 3: Electrical conductivity (a), carrier concentration (b, left) and mobility (b, right) for In-Mo-O (IMO) for samples deposited at 350 °C and 550 °C.

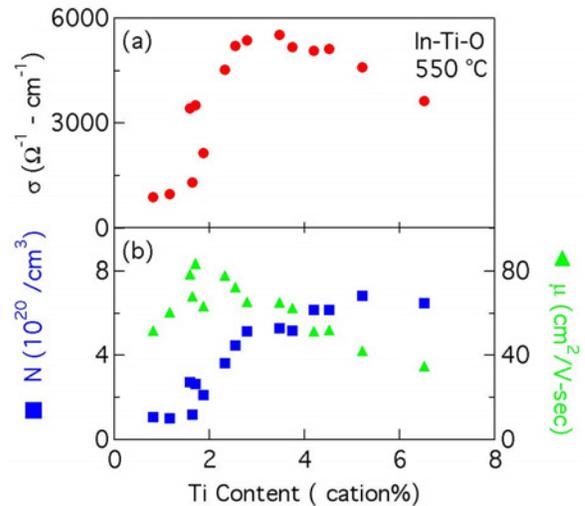


Fig. 4. Electrical conductivity (a), carrier concentration (b, left) and mobility (b, right) for In-Ti-O (ITiO) samples deposited at 550 °C.

Ti. This corresponds to 1.06 electrons / Ti indicating that for these growth conditions, Ti is a very effective dopant for In_2O_3 contributing the expected 1 electron per dopant atom for Ti doping of In_2O_3 .

4. Conclusions

We have employed combinatorial high-throughput approaches to investigate both these areas. Conductivities of $\approx 2500 \text{ } \Omega^{-1}\cdot\text{cm}^{-1}$ have been obtained for In-Zn-O (IZO) films deposited at 100 °C and $> 5000 \text{ } \Omega^{-1}\cdot\text{cm}^{-1}$ for In-Ti-O (ITiO) and In-Mo-O (IMO) films deposited at 550 °C. The highest mobility obtained was $83 \text{ cm}^2/\text{V}\cdot\text{sec}$ for ITiO deposited at 550 °C.

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